

Advance Technical Information

PolarP2[™] Power MOSFET

IXTQ470P2

N-Channel Enhancement Mode Avalanche Rated Fast Intrinsic Diode



$V_{\scriptscriptstyle DSS}$	=	500V
 _{D25}	=	42A
R _{DS(on)}	≤	145m Ω
t _{rr(typ)}	=	400ns

Symbol	Test Conditions	Maximum Ratings		
V _{DSS} V _{DGR}	$T_J = 25^{\circ}\text{C to } 150^{\circ}\text{C}$ $T_J = 25^{\circ}\text{C to } 150^{\circ}\text{C}, R_{GS} = 1\text{M}\Omega$	500 500	V	
V _{GSS}	Continuous Transient	± 30 ± 40	V	
I _{D25}	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 25^{\circ}{\rm C}$, Pulse Width Limited by $T_{\rm JM}$	42 126	A A	
I _A E _{AS}	$T_{c} = 25^{\circ}C$ $T_{c} = 25^{\circ}C$	42 1.3	A J	
dv/dt	$I_{_{S}} \le I_{_{DM}}, \ V_{_{DD}} \le V_{_{DSS}}, T_{_{J}} \le 150^{\circ}C$	10	V/ns	
P_{D}	T _C = 25°C	830	W	
T _J T _{JM} T _{stg}		-55 +150 150 -55 +150	°C °C °C	
T _L T _{SOLD}	Maximum Lead Temperature for Soldering Plastic Body for 10s	300 260	°C °C	
M _d	Mounting Torque	1.13/10	Nm/lb.in.	
Weight		5.5	g	

TO-3P			
			9
	G		
	S	† Tab	

G =	Gate	D	=	Drain
S =	Source	Tab	=	Drain

Features

- Avalanche Rated
- Fast Intrinsic Diode
- Dynamic dv/dt Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

SymbolTest ConditionsChara(T, = 25°C, Unless Otherwise Specified)Min.		cteristic Values			
BV _{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	500	. 71		V
V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250\mu A$	2.5		4.5	V
I _{gss}	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 100	nA
I _{DSS}	$V_{DS} = V_{DSS}, V_{GS} = 0V$			5	μΑ
	T _J = 125°C			50	μΑ
R _{DS(on)}	$V_{GS} = 10V, I_{D} = 0.5 \bullet I_{D25}, \text{ Note 1}$			145	mΩ

TO-3P (IXTQ) Outline



Symbol (T _J = 25°C U	ol Test Conditions Characteristic V 5°C Unless Otherwise Specified) Min. Typ.		Values Max.	
g _{fs}	V _{DS} = 20V, I _D = 0.5 • I _{D25} , Note 1	23	36	S
C _{iss}			5400	pF
C _{oss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		545	pF
C _{rss}			44	pF
t _{d(on)}	Resistive Switching Times		23	ns
t,	$V_{GS} = 10V$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		12	ns
t _{d(off)}			42	ns
t,	$R_{\rm G} = 3\Omega$ (External)		9	ns
$Q_{g(on)}$			88	nC
Q _{gs}	$V_{GS} = 10V$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		30	nC
Q_{gd}	_{jd})		31	nC
R _{thJC}				0.15 °C/W
$\mathbf{R}_{\mathrm{thCS}}$			0.25	°C/W

Source-Drain Diode

Symbol Test Conditions		Characteristic Values			
$(T_J = 25^{\circ}C U)$	Inless Otherwise Specified)	Min.	Тур.	Max.	
I _s	$V_{GS} = 0V$			42	Α
I _{SM}	Repetitive, Pulse Width Limited by $\rm T_{_{\rm JM}}$			168	Α
V _{SD}	$I_F = I_S$, $V_{GS} = 0V$, Note 1			1.5	V
t _{rr}	$I_{F} = 21A, -di/dt = 100A/\mu s$		400		ns
	$V_{R} = 100V, V_{GS} = 0V$				

Note 1. Pulse test, $t \le 300 \mu s$, duty cycle, $d \le 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

